Notice of Allowability	Application No.	Applicant(s)
	10/718,310	KOWALSKI ET AL.
	Examiner	Art Unit
	Tu-Tu Ho	2818
The MAILING DATE of this communication appears on the cover sheet with the correspondence address All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS. This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.		
1. This communication is responsive to <u>Paper filed 11/20/2003</u> .		
2. The allowed claim(s) is/are <u>1-12</u> .		
3. The drawings filed on 20 November 2003 are accepted by the Examiner.		
<ul> <li>4.  Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).</li> <li>a)  All b)  Some* c)  None of the:  1.  Certified copies of the priority documents have been received.  2.  Certified copies of the priority documents have been received in Application No  3.  Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)).  * Certified copies not received:</li> <li>Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application.  THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.</li> </ul>		
5. A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.		
<ul> <li>6. CORRECTED DRAWINGS (as "replacement sheets") must be submitted. <ul> <li>(a) including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached</li> <li>1) hereto or 2) to Paper No./Mail Date</li> <li>(b) including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date</li> <li>Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d).</li> </ul> </li> <li>7. DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.</li> </ul>		
•	6. Interview Summary Paper No./Mail Da 08), 7. Examiner's Amendo	te

## **DETAILED ACTION**

## Allowable Subject Matter

1. Claims 1-12 are allowable over the prior art of record.

The following is an examiner's statement of reasons for allowance: The prior art of record fails to teach or render obvious a memory cell array and a transistor array having all exclusive all limitations as recited in claims 1 and 5, comprising vertical FET transistors each formed of vertical and laterally parallel sections of active webs of semiconductor formed into a depth of a substrate, word lines for the memory cell array of semiconductor memory cells assigned to the transistor array, word line contacts electrically connecting at least some of the word lines to metal tracks of a metal plane superimposed on the transistor array, characterized in that: deep trenches are formed with a substantially identical structure as deep trenches otherwise forming storage capacitors in the memory cell array, except for a buried strap connecting the active web in the memory cell array to polysilicon in the depth of the substrate and that is omitted in the deep trenches of the word line contacts, or that: the word lines for the memory cell array are formed in a common well and run into a second semiconductor well, separate and insulated from the first semiconductor well and having the same conduction type, and the word line contacts connect the word lines to the metal tracks of the metal plane in the second semiconductor well.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue

fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

## Conclusion

- 2. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Copies of the references are not being furnished with this Office Action per MPEP § 707.05(a).
- a) U.S. Patent 6,515,327 to King discloses a trench capacitor with an expanded area for use in a memory cell.
- b) U.S. Patent 6,344,390 to Bostelmann et al. discloses a method of forming a buried strap and its quantum barrier in deep trench cell capacitors.
- 3. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Tu-Tu Ho whose telephone number is (571) 272-1778. The examiner can normally be reached on 6:30 am 5:00 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, DAVID NELMS can be reached on (571) 272-1787. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR

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system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Tu-Tu Ho

August 23, 2004

David Nelms

Supervisory Patent Examiner Technology Center 2800 Page 4